



迈拓电子
MAITUO ELECTRONIC

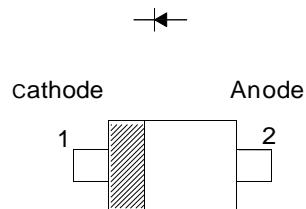
FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING: B0520W: SD

B0530W: SE

B0540W: SF



SOD-123

Maximum Ratings @Ta=25°C

Peak repetitive peak reverse voltage	Symbol	B0520W	B0530W	B0540W	Unit
Working peak reverse voltage	V _{RRM}				
DC Blocking voltage	V _{RWM}	20	30	40	V
	V _R				
RMS reverse voltage reverse voltage (DC)	V _{R(RMS)}	14	20	28	V
Average rectified output current	I _o		0.5		A
Forward surge current peak	I _{FSM}		5.5		A
Power dissipation	P _D		500		mW
Thermal resistance junction to ambient	R _{θJA}		250		°C/W
Junction temperature	T _j		150		°C
Storage temperature	T _{STG}		-55~+150		°C
Voltage rate of change	dv/dt		1000		V/μS

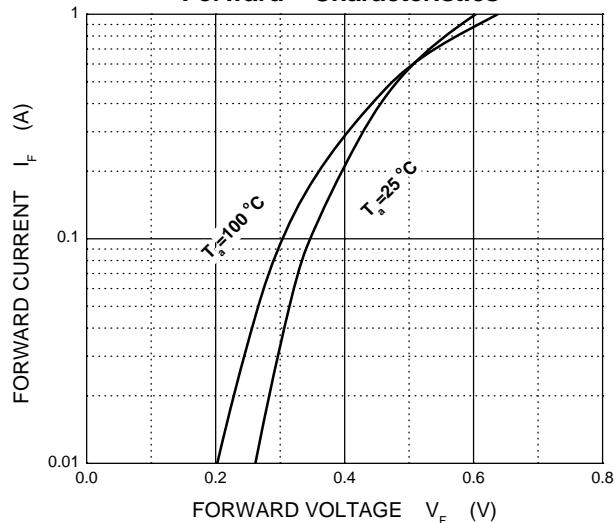
Electrical Characteristics @Ta=25°C

Parameter	Symbol	B0520W	B0530W	B0540W		
Minimum reverse breakdown voltage	V _{(BR)R}	20	--	--	V	I _R =250 μA
		--	30	--		I _R =200 μA
		--	--	40		I _R =20 μA
Forward voltage	V _{F1}	0.32	0.375	--	V	I _F =0.1A
	V _{F2}	0.385	0.430	0.510		I _F =0.5A
	V _{F3}	--	--	0.62		I _F =1A
Reverse current	I _{R1}	75	--	--	μA	V _R =10V
	I _{R2}	--	20	--		V _R =15V
Reverse current	I _{R3}	250	--	10	μA	V _R =20V
	I _{R4}	--	130	--		V _R =30V
	I _{R5}	--	--	20		V _R =40V
Capacitance between terminals	C _T	--	--	170	pF	V _R =0,f=1MHz

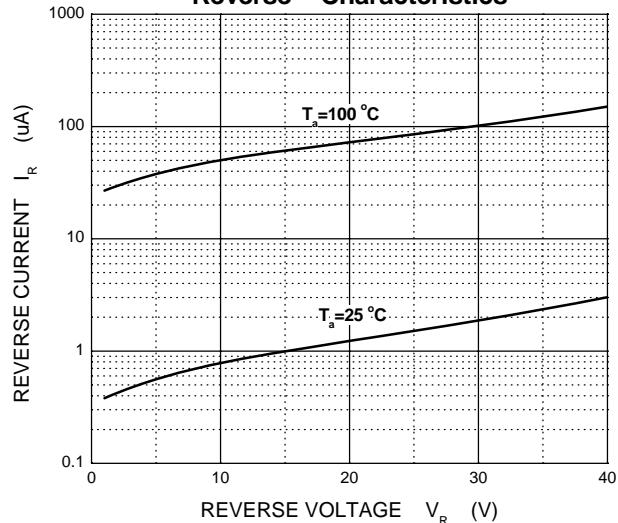


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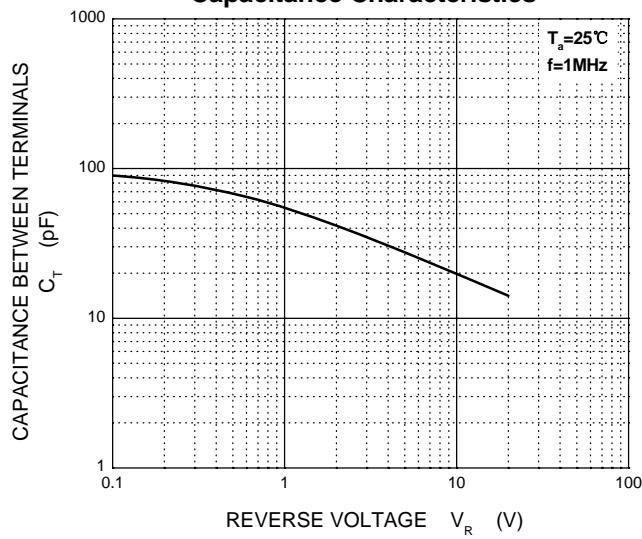
Forward Characteristics



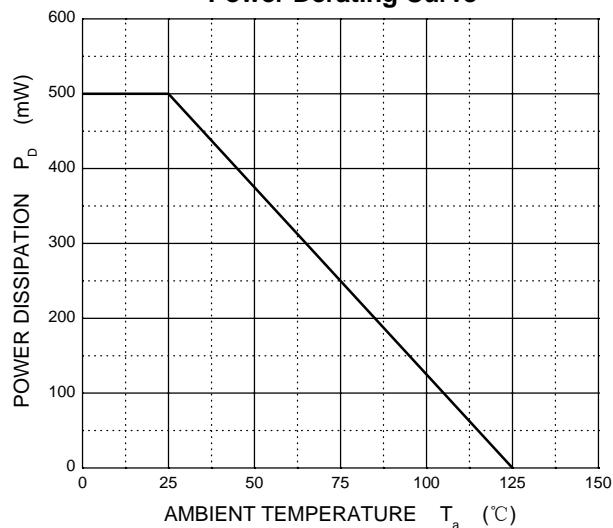
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve



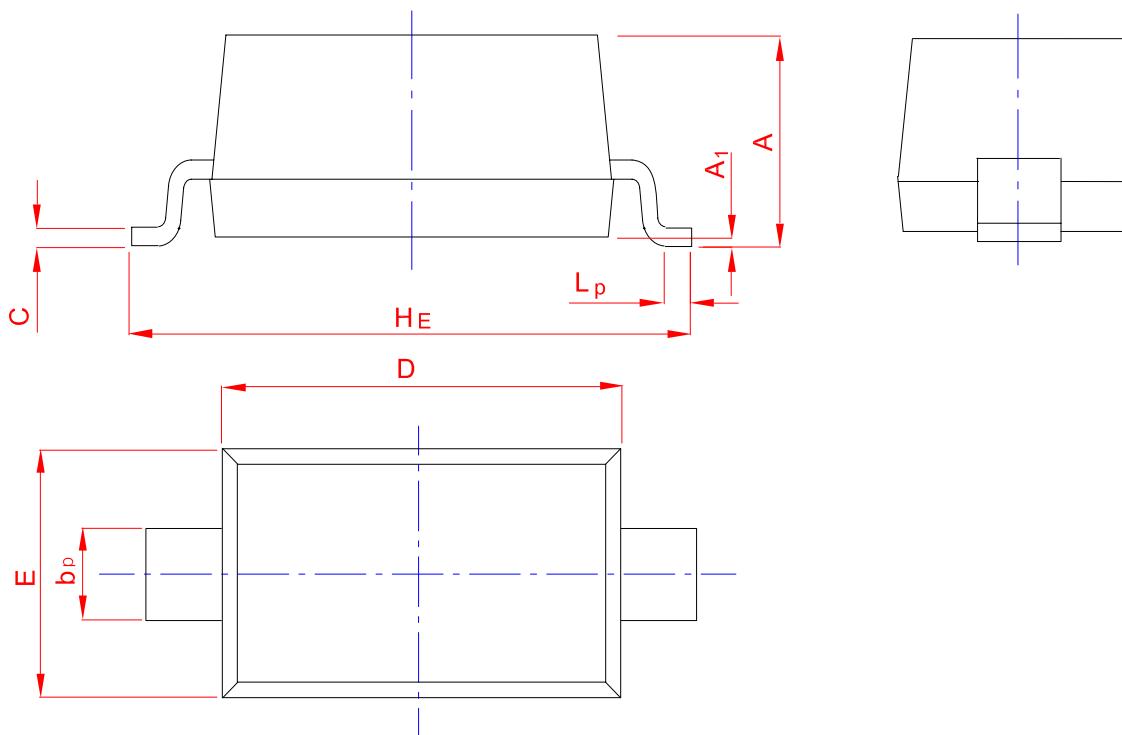


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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UNIT	A	b _p	C	D	E	H _E	A ₁	L _p
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20